# **PSMN012-60YS**



# N-channel LFPAK 60 V, 11.1 m $\Omega$ standard level MOSFET

Rev. 01 — 5 January 2010

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	60	V
$I_D$	drain current	$T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ see <u>Figure 1</u>	-	-	59	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	89	W
Tj	junction temperature		-55	-	175	°C
Avalanci	he ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;}$ $I_D = 59 \text{ A; } V_{sup} \le 60 \text{ V;}$ $R_{GS} = 50 \Omega$	-	-	71	mJ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 30 \text{ A};$	-	6.4	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; see <u>Figure 14</u> and <u>15</u>	-	28.4	-	nC



### N-channel LFPAK 60 V, 11.1 m $\Omega$ standard level MOSFET

Table 1. Quick reference ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{ or } 12}$	-	-	17.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 13</u>	-	8	11.1	mΩ

## 2. Pinning information

Table 2. Pinning information

		<u>'</u>		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb (	D
3	S	source		$G \longrightarrow \overline{A}$
4	G	gate	9	ŭ-Ţ-
mb D		mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package	Package							
	Name	Description	Version						
PSMN012-60YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669						

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## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	60	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	60	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	-	42	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	-	59	Α
I <sub>DM</sub>	peak drain current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	236	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	89	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-dr	ain diode				
I <sub>S</sub>	source current	$T_{mb} = 25  ^{\circ}C$	-	59	Α
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	236	Α
Avalanche	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 59 A; $V_{sup}$ ≤ 60 V; $R_{GS}$ = 50 $\Omega$	-	71	mJ

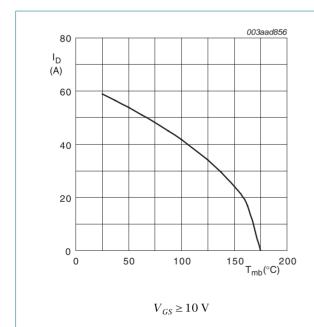


Fig 1. Continuous drain current as a function of mounting base temperature

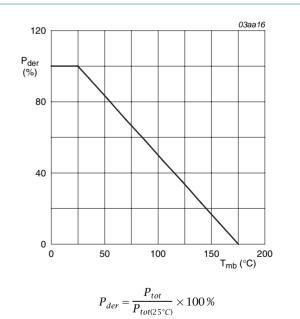


Fig 2. Normalized total power dissipation as a function of mounting base temperature

N-channel LFPAK 60 V, 11.1 mΩ standard level MOSFET

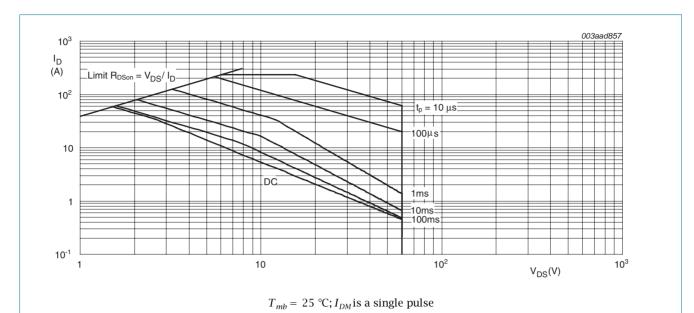


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	8.0	1.68	K/W

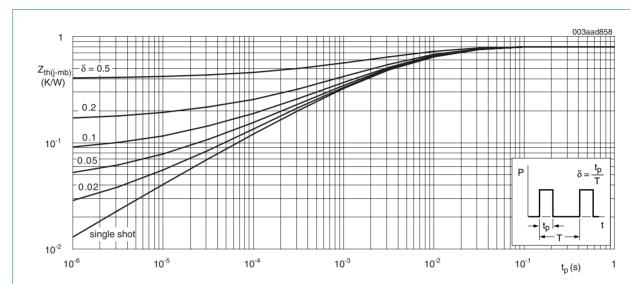


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

## 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	54	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; see <u>Figure 10</u> and <u>11</u>	2	3	4	V
V <sub>GSth</sub>		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ °C}$ ; see Figure 11	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 11	0.95	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.03	2	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12	-	17	25.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see Figure 12	-	-	17.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 13}{\text{ Figure } 13}$	-	8	11.1	mΩ
$R_G$	gate resistance	f = 1 MHz	-	0.66	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> and <u>15</u>	-	28.4	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	23.3	-	nC
$Q_{GS}$	gate-source charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> and <u>15</u>	-	8.75	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u>	-	4.9	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	3.9	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> and <u>15</u>	-	6.4	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 30 \text{ V}$ ; see Figure 14 and 15	-	4.8	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 °C;$	-	1685	-	pF
C <sub>oss</sub>	output capacitance	see Figure 16		245	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	140	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1 \Omega; V_{GS} = 10 \text{ V};$	-	15.2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	12.6	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	28.7	-	ns
t <sub>f</sub>	fall time		-	8.2	-	ns

### N-channel LFPAK 60 V, 11.1 mΩ standard level MOSFET

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 15 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 17</u>	-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	35	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 \text{ V}$	-	41	-	nC

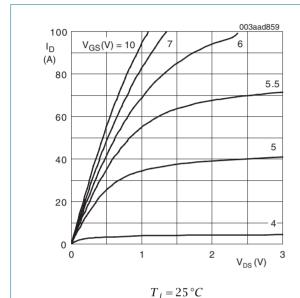
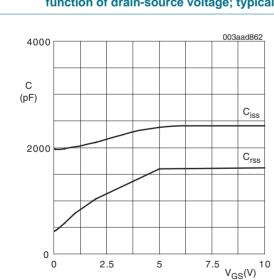
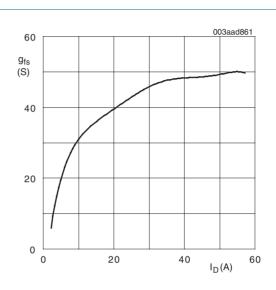


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

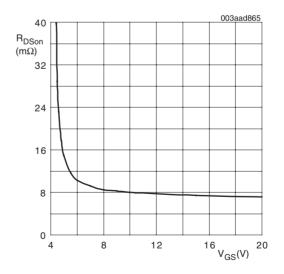


 $V_{\it DS} = 0~{\rm V;~f} = 1~{\rm MHz}$  Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage, typical values



 $T_i = 25$  °C;  $V_{DS} = 15$  V

Fig 6. Forward transconductance as a function of drain current; typical values



 $T_j = 25$  °C;  $I_D = 10$  A

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

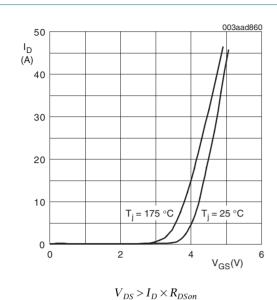
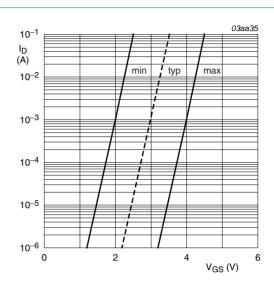
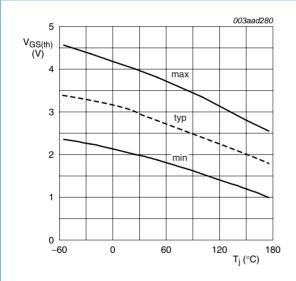


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



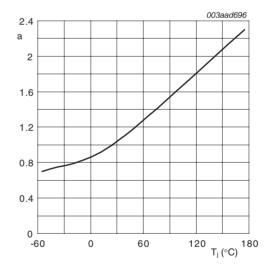
 $T_j=25\,^{\circ}C; V_{DS}=5V$ 

Fig 10. Sub-threshold drain current as a function of gate-source voltage



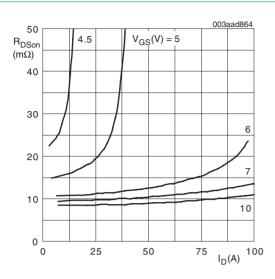
 $I_D = 1 \, mA; V_{DS} = V_{GS}$ 

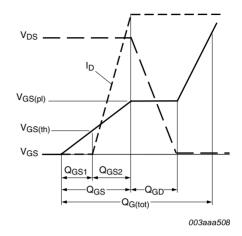
Fig 11. Gate-source threshold voltage as a function of junction temperature



 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$ 

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

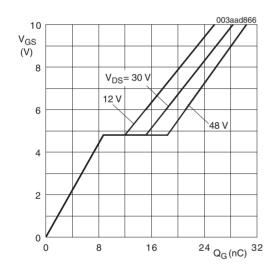


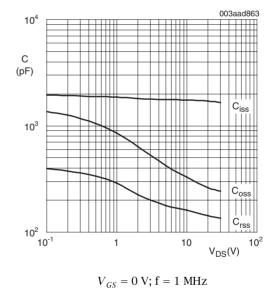


 $T_j = 25 \,^{\circ}C$ 

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions





 $T_j = 25 \, ^{\circ}\text{C}; I_D = 30 \, \text{A}$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values



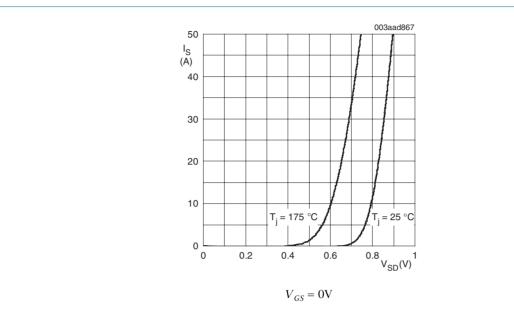
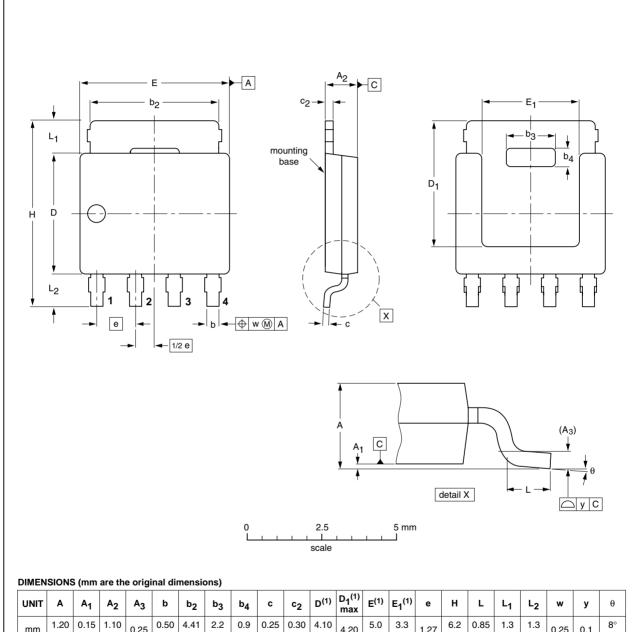


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

## Package outline

### Plastic single-ended surface-mounted package (LFPAK); 4 leads

**SOT669** 



UNIT	Α	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b	b <sub>2</sub>	b <sub>3</sub>	b <sub>4</sub>	С	c <sub>2</sub>	D <sup>(1)</sup>	D <sub>1</sub> <sup>(1)</sup> max	E <sup>(1)</sup>	E <sub>1</sub> <sup>(1)</sup>	е	Н	L	L <sub>1</sub>	L <sub>2</sub>	w	у	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

#### Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT669		MO-235				<del>04-10-13</del> 06-03-16

Fig 18. Package outline SOT669 (LFPAK)

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N-channel LFPAK 60 V, 11.1 m $\Omega$  standard level MOSFET

## 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN012-60YS_1	20100105	Product data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# **PSMN012-60YS**

### N-channel LFPAK 60 V, 11.1 m $\Omega$ standard level MOSFET

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- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



**«JONHON»** (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«**FORSTAR**» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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